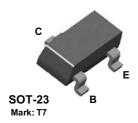


BSR15



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifier and switches requiring collector currents to 500 mA. Sourced from Process 63. See BCW68G for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units		
V_{CEO}	Collector-Emitter Voltage	40	V		
V _{CBO}	Collector-Base Voltage	60	V		
V _{EBO}	Emitter-Base Voltage	5.0	V		
I _C	Collector Current - Continuous	800	mA		
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C		

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		*BSR15		
P _D	Total Device Dissipation	350	mW	
	Derate above 25°C	2.8	mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	°C/W	

^{*}Device mounted on FR-4 PCB 40 mm X 40 mm X 1.5 mm.

PNP General Purpose Amplifier

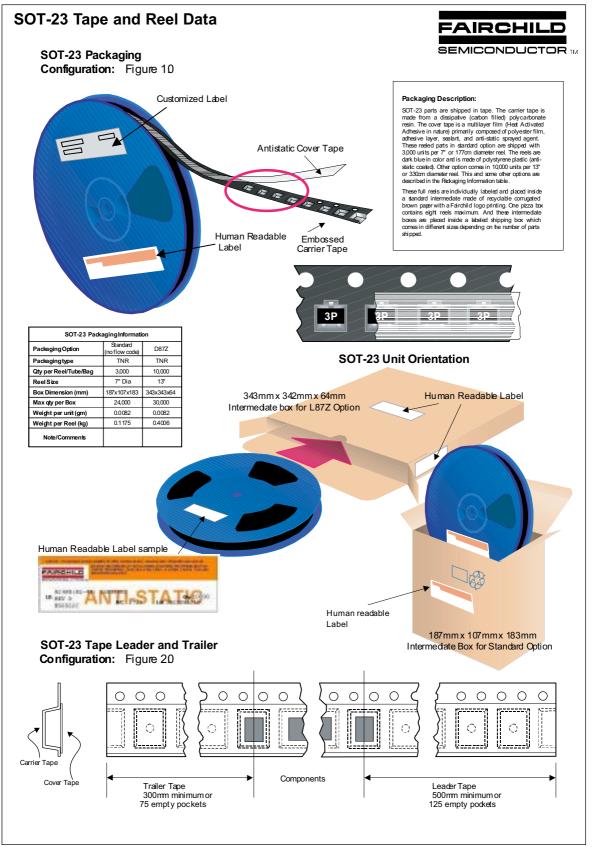
(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
		ı			
OFF CHAI	RACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_{C} = 100 \mu A, I_{B} = 0$	60		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu \text{A}, \ I_{\rm E} = 0$	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \mu A, I_C = 0$	5.0		V
I _{CBO}	Collector-Cutoff Current	V _{CB} = 50 V V _{CB} = 50 V, T _A = 150°C		20 20	nA μA
I _{CEX}	Collector-Cutoff Current	V _{CE} = 30 V, V _{EB} = 0.5 V		50	nA
I _{BEX}	Reverse Base Current	V _{CE} = 30 V, V _{EB} = 3.0 V		50	nA
ON CHAR	ACTERISTICS DC Current Gain	I _C = 0.1 mA, V _{CE} = 10 V I _C = 1.0 mA, V _{CE} = 10 V	35 50		
		I_C = 10 mA, V_{CE} = 10 V I_C = 150 mA, V_{CE} = 10 V I_C = 500 mA, V_{CE} = 10 V	75 100 30	300	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$ $I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.4 1.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 150 mA, I _B = 15 mA I _C = 500 mA, I _B = 50 mA		1.3 2.6	V
SMALL SI	GNAL CHARACTERISTICS				
f _T	Current Gain - Bandwidth Product	$I_C = 50 \text{ mA}, V_{CE} = 20,$ f = 100 MHz, $T_A = 25^{\circ}C$	200		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		8.0	pF
C _{eb}	Emitter-Base Capacitance	$V_{EB} = 2.0 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		30	pF
SWITCHIN	NG CHARACTERISTICS				
t _{on}	Turn-on Time	$V_{CC} = 30 \text{ V}, I_{C} = 150 \text{ mA},$		45	ns
t _d	Delay Time	I _{B1} = 15 mA		10	ns
t _r	Rise Time			40	ns
$t_{\rm off}$	Turn-off Time	$V_{CC} = 6.0 \text{ V}, I_{C} = 150 \text{ mA}$		100	ns
ts	Storage Time	$I_{B1} = I_{B2} = 15 \text{ mA}$		80	ns
t _f	Fall Time			30	ns

 $\textbf{NOTE:} \ All \ voltages \ (V) \ and \ currents \ (A) \ are \ negative \ polarity \ for \ PNP \ transistors.$

Spice Model

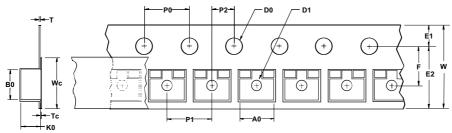
PNP (Is=650.6E-18 Xti=3 Eg=1.11 Vaf=115.7 Bf=231.7 Ne=1.829 Ise=54.81f Ikf=1.079 Xtb=1.5 Br=3.563 Nc=2 Isc=0 Ikr=0 Rc=.715 Cjc=14.76p Mjc=.5383 Vjc=.75 Fc=.5 Cje=19.82p Mje=.3357 Vje=.75 Tr=111.3n Tf=603.7p Itf=.65 Vtf=5 Xtf=1.7 Rb=10)



SOT-23 Tape and Reel Data, continued

SOT-23 Embossed Carrier Tape

Configuration: Figure 3.0



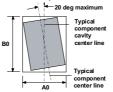
User Direction of Feed

Dimensions are in millimeter														
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	т	Wc	Тс
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

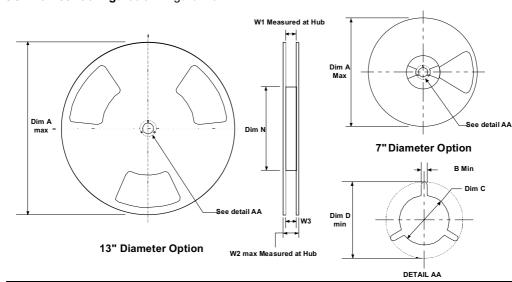


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

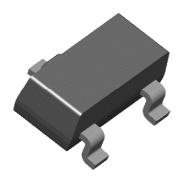
SOT-23 Reel Configuration: Figure 4.0

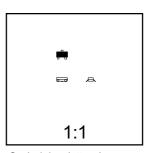


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 – 0.429 7.9 – 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9



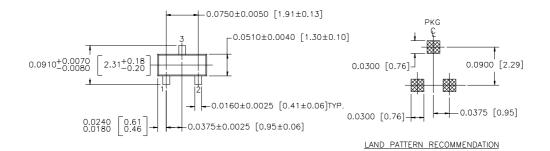
SOT-23 (FS PKG Code 49)

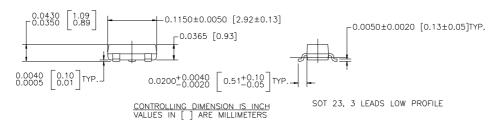




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.0082





NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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